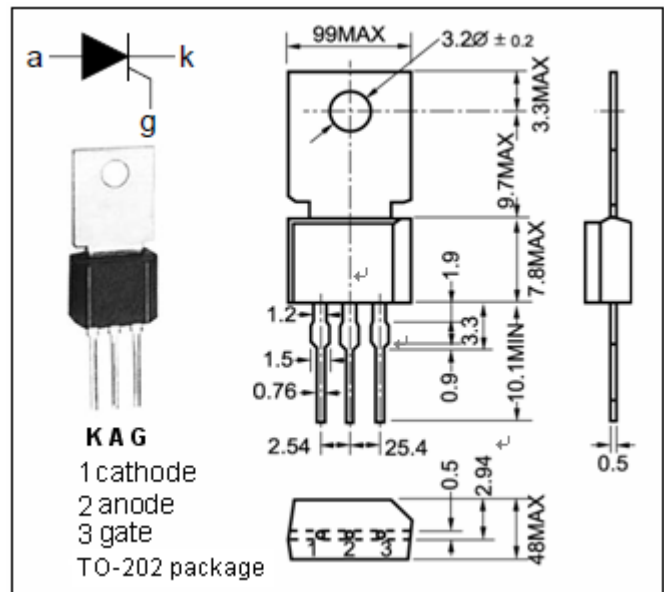


isc Thyristors

2P4M

APPLICATIONS

- Highly sensitive triggering levels
- For capacitive discharge ignitions, motor control in kitchen aids, overvoltage crowbar protection in low power supplies applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	400	V
V_{RRM}	Repetitive peak reverse voltage	400	V
$I_{\text{T(AV)}}$	On-state current 180° conduction angle	4	A
I_{TSM}	Non-repetitive surge peak on-state current $t=20\text{ms}$	20	A
$P_{\text{G(AV)}}$	Average gate power dissipation $T_j = 125^{\circ}\text{C}$	0.2	W
T_j	Junction temperature	125	
T_{stg}	Storage temperature	-40 to + 150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_c=25^{\circ}\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	$V_{\text{RM}}=V_{\text{RRM}}, R_{\text{GK}}=1\text{k}\Omega$ $V_{\text{RM}}=V_{\text{RRM}}, R_{\text{GK}}=1\text{k}\Omega, T_j=125^{\circ}\text{C}$		10 500	μA
I_{DRM}	Repetitive peak off-state current	$V_{\text{DM}}=V_{\text{DRM}}, R_{\text{GK}}=1\text{k}\Omega$ $V_{\text{DM}}=V_{\text{DRM}}, R_{\text{GK}}=1\text{k}\Omega, T_j=125^{\circ}\text{C}$		10 500	μA
V_{TM}	On-state voltage	$I_{\text{TM}}=4\text{A}$		1.8	V
I_{GT}	Gate-trigger current	$V_{\text{DM}}=12\text{V}; R_{\text{L}}=140\Omega$		200	μA
V_{GT}	Gate-trigger voltage	$V_{\text{DM}}=12\text{V}; R_{\text{L}}=140\Omega$		0.8	V